

8. (Amended) A multi-layer electrode for an integrated circuit, comprising:

- a conductive barrier layer;
- a first conductive liner deposited over the conductive barrier layer, the first conductive liner comprising a molecular grain structure having a plurality of columns;
- a second conductive liner deposited over the first conductive liner, the second conductive liner comprising a conductive oxide; and
- a conductive layer deposited on the second conductive liner, the conductive layer comprising a molecular grain structure having a plurality of columns, wherein the columns of the conductive layer are not aligned with the columns of the first conductive liner.

25. (New) The multi-layer electrode according to Claim 1, wherein the second conductive liner comprises a thickness such that the second conductive liner is etchable by the same etchant gas used to etch the first conductive liner and the conductive layer.

26. (New) The multi-layer electrode according to Claim 1, wherein the conductive layer comprises a molecular grain structure having columns, the conductive layer including a top surface; wherein the first conductive liner comprises a molecular grain structure having columns; wherein the columns of the conductive layer are not aligned with the columns of the first conductive liner; and wherein the second conductive liner prevents diffusion of oxide from the conductive layer top surface through the conductive layer to the conductive barrier layer.

27. (New) The multi-layer electrode according to Claim 8, wherein the second conductive liner comprises a thickness such that the second conductive liner is etchable by the same etchant gas used to etch the first conductive liner and the conductive layer.

28. (New) An electrode for a semiconductor device, comprising:

a conductive barrier layer;

a platinum liner formed over the conductive barrier layer, the platinum liner comprising a molecular grain structure having a plurality of columns;

a conductive oxide formed over the platinum liner, the conductive oxide having a thickness of 20-50 Angstroms; and

a platinum layer formed over the conductive oxide, the platinum layer comprising a molecular grain structure having a plurality of columns, wherein the columns of the platinum layer are not aligned with the columns of the platinum liner.

29. (New) The multi-layer electrode according to Claim 28 wherein the second conductive liner comprises IrO_2 or RuO_2 .

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C2

30. (New) A multi-layer electrode for an integrated circuit, comprising:

a conductive barrier layer;

a first conductive liner deposited over the conductive barrier layer;

a second conductive liner deposited over the first conductive liner, the second conductive liner comprising a conductive oxide, the second conductive liner having a thickness of 20-50 Angstroms; and

a conductive layer deposited on the second conductive liner.

In the specification:

Please replace the paragraph beginning on page 10, line 6, with the following:

A layer of conductive material 344 is deposited over the second conductive liner 342.

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Conductive layer 344 preferably comprises Pt, and may alternatively comprise other conductive materials such as Ir, Ru, Pd or combinations thereof, for example. Preferably, conductive material 344 comprises 1500-3500 Angstroms of Pt, and more preferably comprises 2200 Angstroms of Pt.

REMARKS

Claims 1-13 and 21-30 are pending in the present application. Claim 8 and the specification are amended herein. Claims 25-30 are added herein. The Applicants respectfully request